MMBT6428LT1G, MMBT6429LT1G, NSVMMBT6429LT1G

Amplifier Transistors

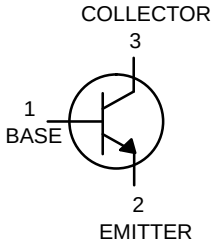
NPN Silicon

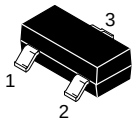
ON Semiconductor®

www.onsemi.com

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC Q101 Qualified and PPAP Capable
- These Devices are Pb Free, Halogen Free/BFR Free and are RoHS Compliant





SOT 23 (TO 236)
CASE 318
STYLE 6

MAXIMUM RATINGS

Rating	Symbol	6428LT1	6429LT1	Unit
Collector Emitter Voltage	V_{CEO}	50	45	Vdc
Collector Base Voltage	V_{CBO}	60	55	Vdc
Emitter Base Voltage	V_{EBO}	6.0		Vdc
Collector Current Continuous	I_C	200		mAdc

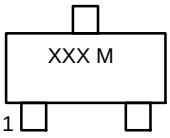
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Total Device Dissipation FR 5 Board (Note 1) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction to Ambient	R_{JA}	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	R_{JA}	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	55 to +150	°C

1. FR 5 = 1.0 0.75 0.062 in.
2. Alumina = 0.4 0.3 0.024 in. 99.5% alumina.

MARKING DIAGRAM



XXX = Specific Device Code
MMBT6428LT1 1KM
NSV/MMBT6429LT1 M1L
M = Date Code*
= Pb Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping †
MMBT6428LT1G	SOT 23 (Pb Free)	3000 Tape & Reel
MMBT6429LT1G	SOT 23 (Pb Free)	3000 Tape & Reel
NSVMMBT6429LT1G	SOT 23 (Pb Free)	3000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector Emitter Breakdown Voltage		$V_{(BR)CEO}$			Vdc
(I_C = 1.0 mAdc, I_B = 0)	MMBT6428		50		
(I_C = 1.0 mAdc, I_B = 0)	MMBT6429 / NSVMMBT6429		45		
Collector Base Breakdown Voltage		$V_{(BR)CBO}$			Vdc
(I_C = 0.1 mAdc, I_E = 0)	MMBT6428		60		
(I_C = 0.1 mAdc, I_E = 0)	MMBT6429 / NSVMMBT6429		55		
Collector Cutoff Current		I_{CES}			Adc
(V_{CE} = 30 Vdc)				0.1	
Collector Cutoff Current		I_{CBO}			Adc
(V_{CB} = 30 Vdc, I_E = 0)				0.01	
Emitter Cutoff Current		I_{EBO}			Adc
(V_{EB} = 5.0 Vdc, I_C = 0)				0.01	
ON CHARACTERISTICS					
DC Current Gain		h_{FE}			
(I_C = 0.01 mAdc, V_{CE} = 5.0 Vdc)	MMBT6428		250		
	MMBT6429 / NSVMMBT6429		500		
(I_C = 0.1 mAdc, V_{CE} = 5.0 Vdc)	MMBT6428		250	650	
	MMBT6429 / NSVMMBT6429		500	1250	
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	MMBT6428		250		
	MMBT6429 / NSVMMBT6429		500		
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	MMBT6428		250		
	MMBT6429 / NSVMMBT6429		500		
Collector Emitter Saturation Voltage		$V_{CE(sat)}$			Vdc
(I_C = 10 mAdc, I_B = 0.5 mAdc)				0.2	
(I_C = 100 mAdc, I_B = 5.0 mAdc)				0.6	
Base Emitter On Voltage		$V_{BE(on)}$			Vdc
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)			0.56	0.66	
SMALL SIGNAL CHARACTERISTICS					
Current Gain Bandwidth Product		f_T			MHz
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 100 MHz)			100	700	
Output Capacitance		C_{obo}			pF
(V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)				3.0	
Input Capacitance		C_{ibo}			pF
(V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)				8.0	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

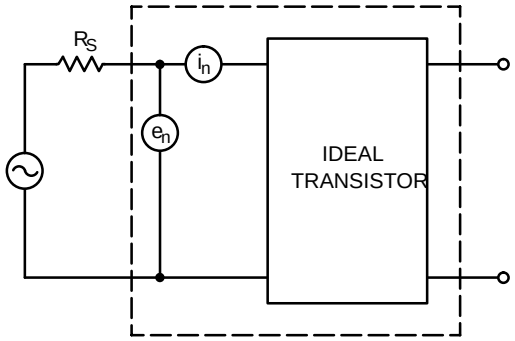


Figure 1. Transistor Noise Model

NOISE CHARACTERISTICS

(V_{CE} = 5.0 Vdc, T_A = 25°C)

NOISE VOLTAGE

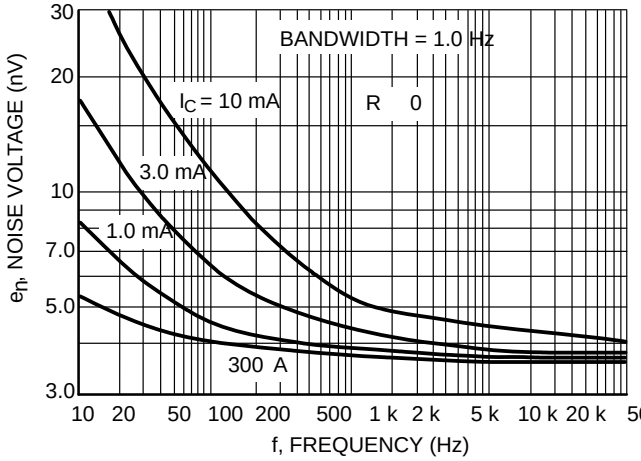


Figure 2. Effects of Frequency

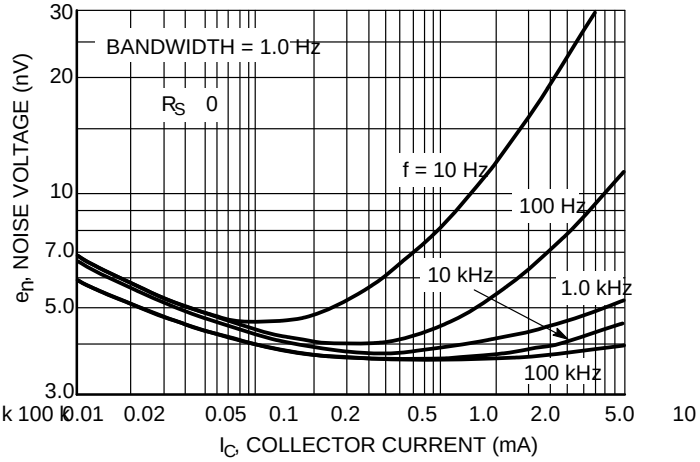


Figure 3. Effects of Collector Current

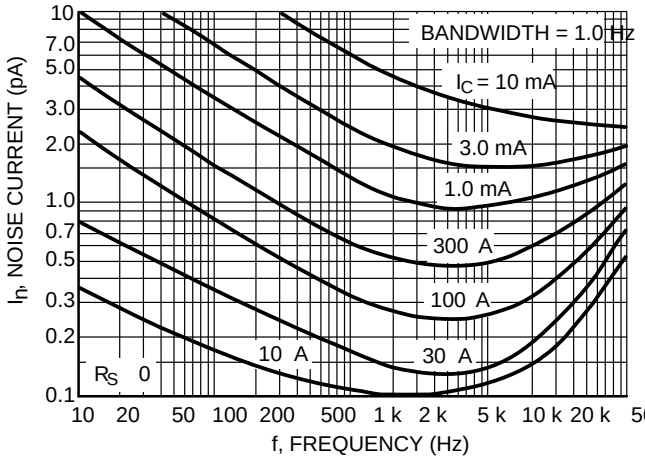


Figure 4. Noise Current

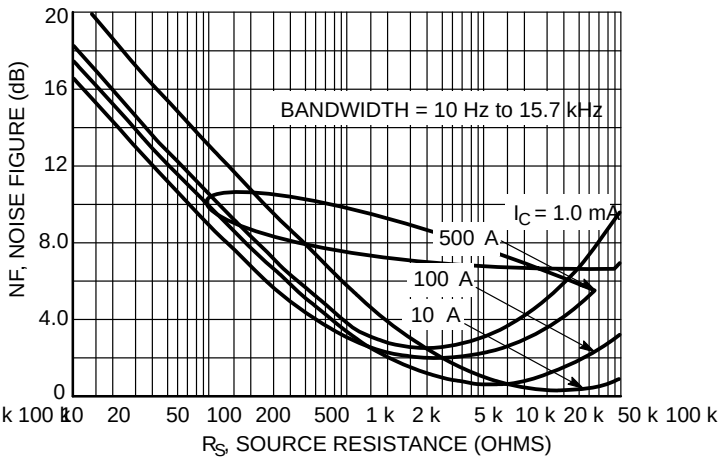


Figure 5. Wideband Noise Figure

100 Hz NOISE DATA

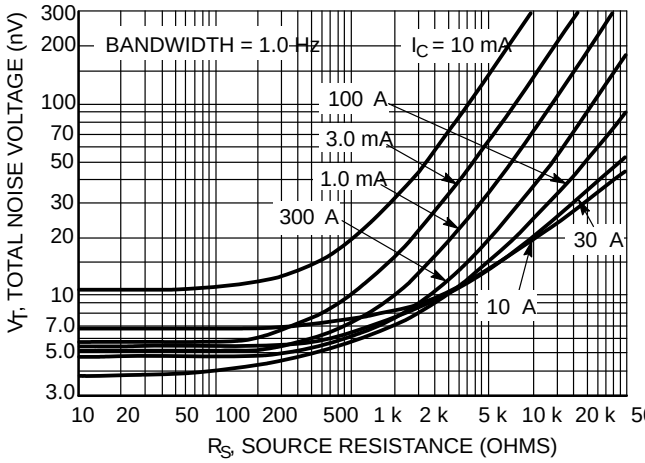


Figure 6. Total Noise Voltage

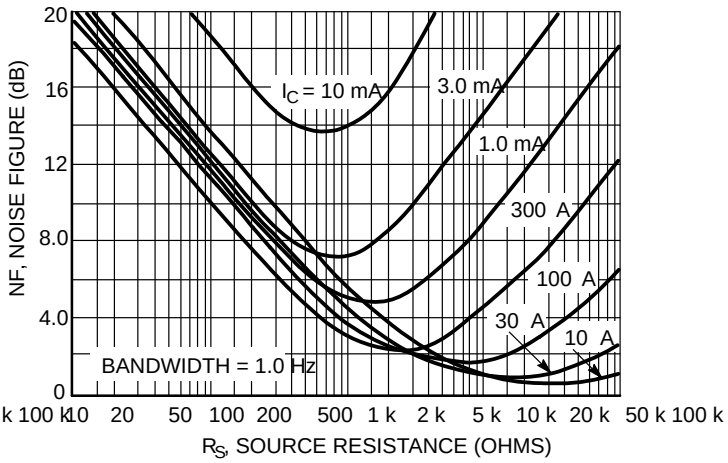


Figure 7. Noise Figure

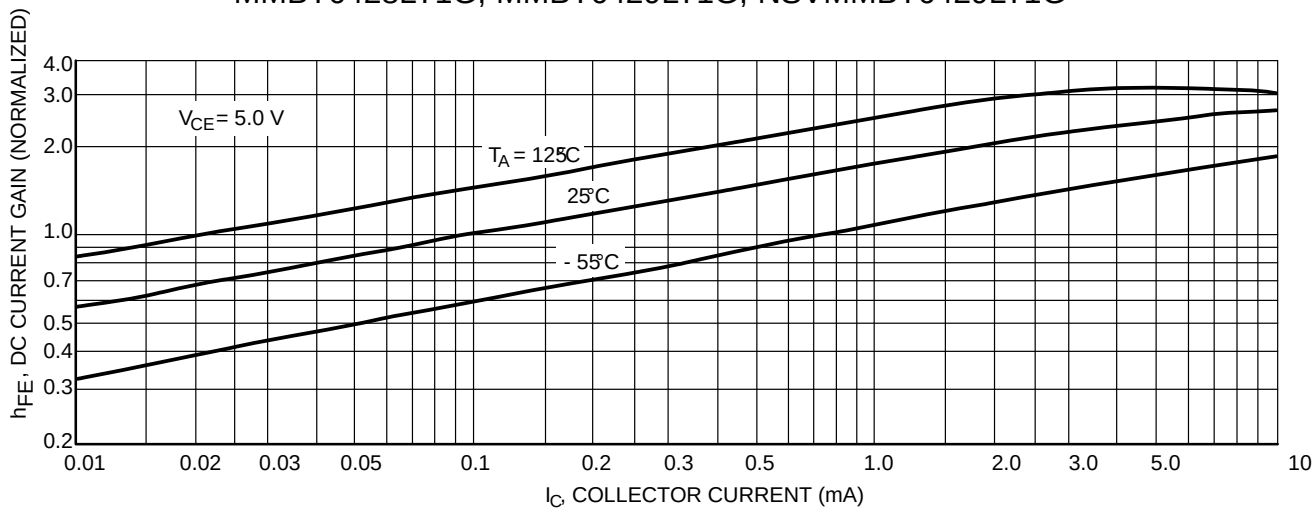


Figure 8. DC Current Gain

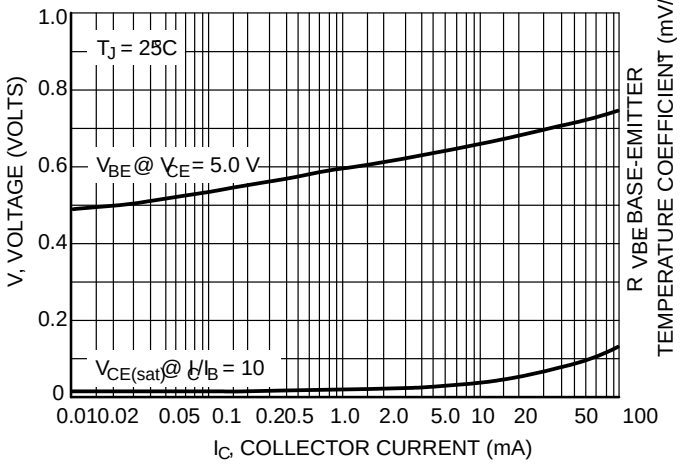


Figure 9. “On” Voltages

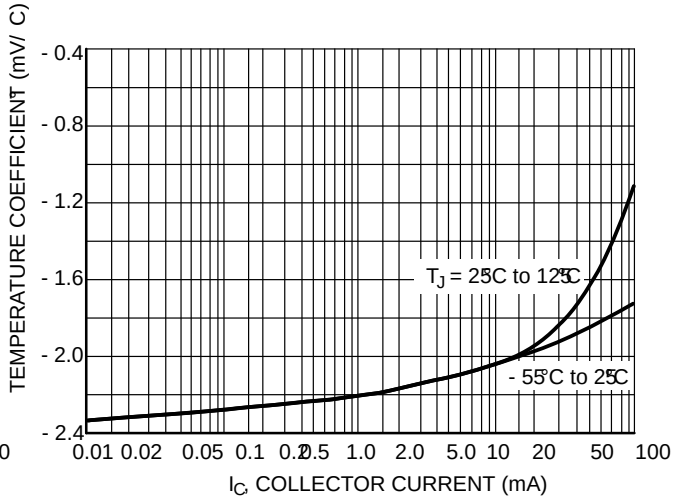


Figure 10. Temperature Coefficients

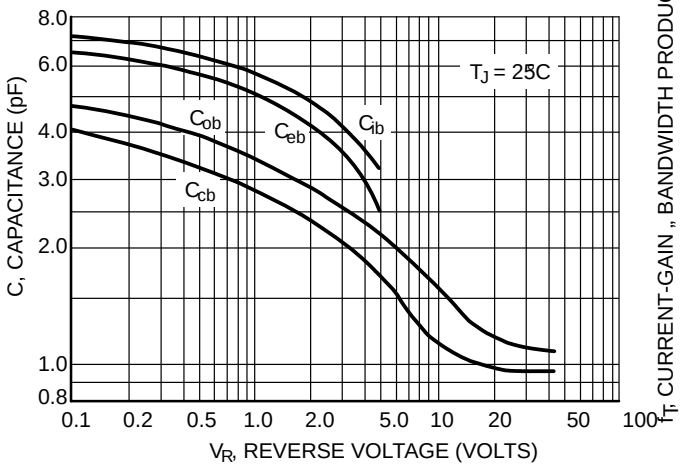


Figure 11. Capacitance

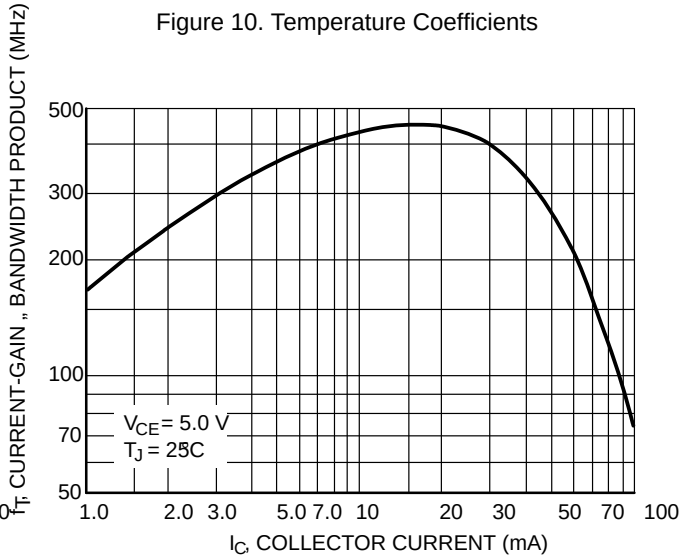
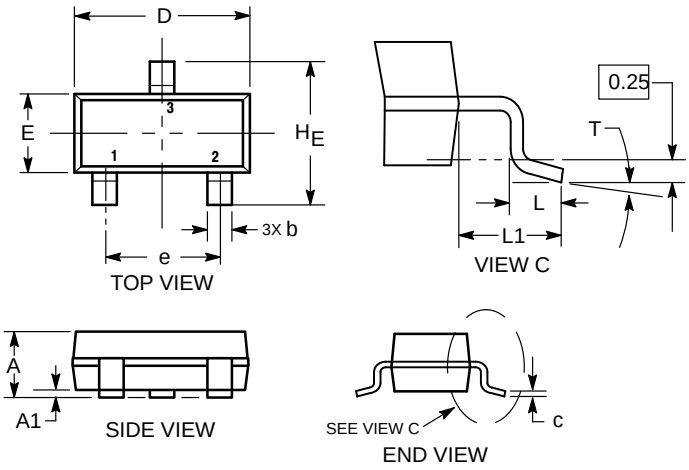


Figure 12. Current Gain — Bandwidth Product

PACKAGE DIMENSIONS

SOT 23 (TO 236)
CASE 318 08
ISSUE AR

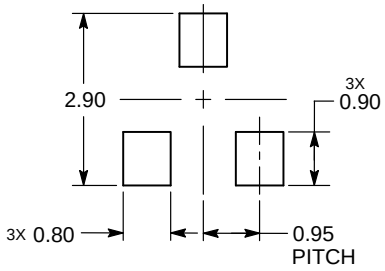


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H_E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°		10 °	0 °		10 °

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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